**Key Parameters**

V_{DRM} / V_{RRM}	1800 V
I_{TAVM}	350 A ($T_C=100\text{ °C}$)
I_{TSM}	13000 A
V_{T0}	0,75 V
r_T	0,4 m Ω
R_{thJC}	0,124 K/W
Base plate	50 mm



For type designation please refer to actual short form catalog

<http://www.ifbip.com/catalog>

Merkmale

- Druckkontakt-Technologie für hohe Zuverlässigkeit
- Advanced Medium Power Technology (AMPT)
- Industrie-Standard-Gehäuse
- Elektrisch isolierte Bodenplatte

Features

- Pressure contact technology for high reliability
- Advanced Medium Power Technology (AMPT)
- Industrial standard package
- Electrically insulated base plate

Typische Anwendungen

- Gleichrichter für Antriebsapplikationen
- Kurzschließer-Applikationen
- Gleichrichter für UPS
- Batterieladegleichrichter

Typical Applications

- Rectifier for drives applications
- Crowbar applications
- Rectifiers for UBS
- Battery chargers

content of customer DMX code	DMX code digit	DMX code digit quantity
serial number	1..5	5
SAP material number	6..12	7
Internal production order number	13..20	8
datecode (production year)	21..22	2
datecode (production week)	23..24	2



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Datenblatt / Data sheet



Netz-Dioden-Modul
Rectifier Diode Module

DD350N

Infineon Technologies Bipolar
GmbH & Co. KG

DD350N

Elektrische Eigenschaften / Electrical properties

Höchstzulässige Werte / Maximum rated values

Periodische Spitzensperrspannung repetitive peak reverse voltages	$T_{vj} = -40^{\circ}\text{C} \dots T_{vj\text{max}}$	V_{RRM}	1200 1600	1400 1800	V V
Stoßspitzensperrspannung non-repetitive peak reverse voltage	$T_{vj} = +25^{\circ}\text{C} \dots T_{vj\text{max}}$	V_{RSM}	1300 1700	1500 1900	V V
Durchlaßstrom-Grenzeffektivwert maximum RMS on-state current		I_{FRMSM}		550	A
Dauergrenzstrom average on-state current	$T_C = 100^{\circ}\text{C}$	I_{FAVM}		350	A
Stoßstrom-Grenzwert surge current	$T_{vj} = 25^{\circ}\text{C}, t_p = 10\text{ms}$ $T_{vj} = T_{vj\text{max}}, t_p = 10\text{ms}$	I_{FSM}		13000 11000	A A
Grenzlastintegral I^2t -value	$T_{vj} = 25^{\circ}\text{C}, t_p = 10\text{ms}$ $T_{vj} = T_{vj\text{max}}, t_p = 10\text{ms}$	I^2t		845000 605000	A ² s A ² s

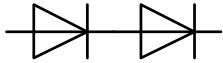
Charakteristische Werte / Characteristic values

Durchlaßspannung on-state voltage	$T_{vj} = T_{vj\text{max}}, I_F = 1000\text{A}$	V_F	max.	1,28	V
Schleusenspannung threshold voltage	$T_{vj} = T_{vj\text{max}}$	$V_{(TO)}$	max.	0,75	V
Ersatzwiderstand slope resistance	$T_{vj} = T_{vj\text{max}}$	r_T	max.	0,4	m Ω
Sperrstrom reverse current	$T_{vj} = T_{vj\text{max}}, V_R = V_{RRM}$	i_R	max.	30	mA
Isolations-Prüfspannung insulation test voltage	RMS, $f = 50\text{Hz}, t = 1\text{ sec}$ RMS, $f = 50\text{Hz}, t = 1\text{ min}$	V_{ISOL}		3,6 3,0	kV kV

Thermische Eigenschaften / Thermal properties

Innerer Wärmewiderstand thermal resistance, junction to case	pro Modul / per Module, $\Theta = 180^{\circ}\text{ sin}$ pro Zweig / per arm, $\Theta = 180^{\circ}\text{ sin}$ pro Modul / per Module, DC pro Zweig / per arm, DC	R_{thJC}	max.	0,065 0,130 0,062 0,124	K/W K/W K/W K/W
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	pro Modul / per Module pro Zweig / per arm	R_{thCH}	max.	0,02 0,04	K/W K/W
Höchstzulässige Sperrschichttemperatur maximum junction temperature		$T_{vj\text{max}}$		150	$^{\circ}\text{C}$
Betriebstemperatur operating temperature		$T_{c\text{op}}$		- 40...+150	$^{\circ}\text{C}$
Lagertemperatur storage temperature		T_{stg}		- 40...+150	$^{\circ}\text{C}$

prepared by:	HR	date of publication:	2018-07-30
approved by:	ML	revision:	3.2



Datenblatt / Data sheet




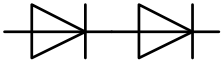
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Mechanische Eigenschaften / Mechanical properties

Gehäuse, siehe Anlage case, see annex			Seite 3 page 3	
Si-Element mit Druckkontakt Si-pellet with pressure contact				
Innere Isolation internal insulation	Basisisolierung (Schutzklasse 1, EN 61140) Basic insulation (class 1, IEC 61140)		AIN	
Anzugsdrehmoment für mechanische Anschlüsse mounting torque	Toleranz ±15%	M1	6	Nm
Anzugsdrehmoment für elektrische Anschlüsse terminal connection torque	Toleranz ±10%	M2	12	Nm
Gewicht weight			typ. 800	g
Kriechstrecke creepage distance			17	mm
Schwingfestigkeit vibration resistance	f = 50Hz		50	m/s ²
	file-No.		E 83335	



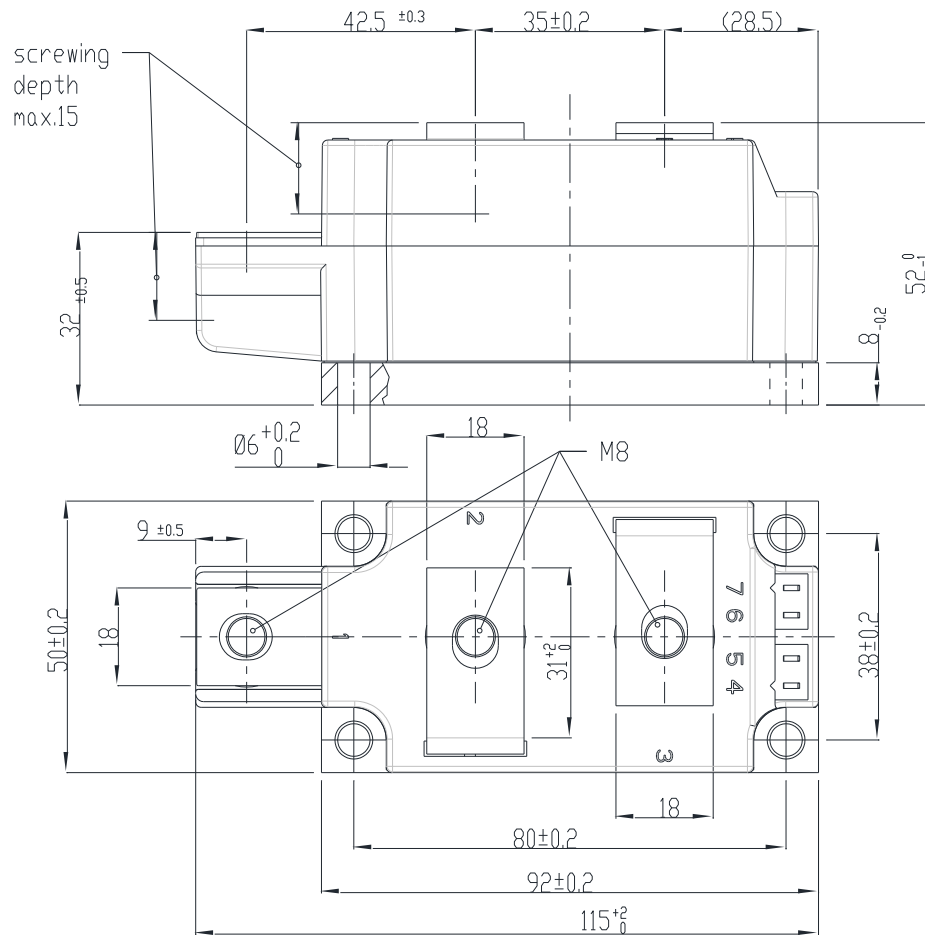
Datenblatt / Data sheet



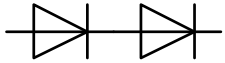
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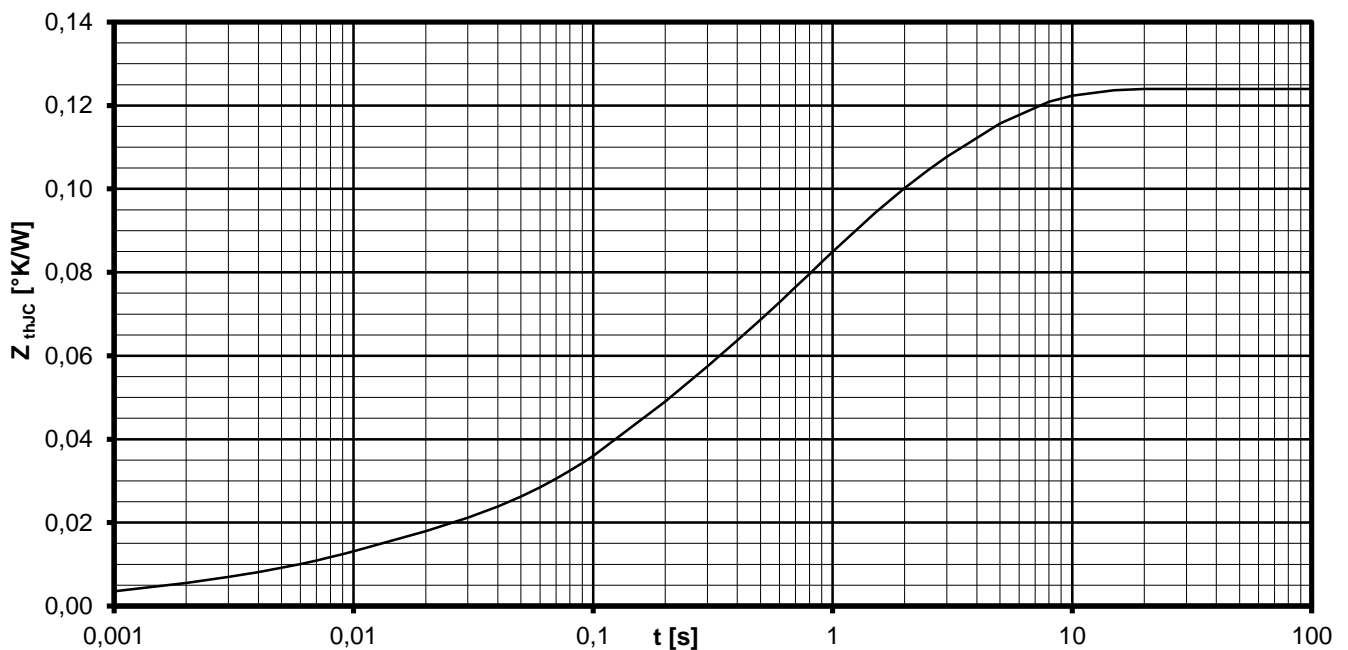
<p>DD</p>		



Analytische Elemente des transienten Wärmewiderstandes Z_{thJC} für DC
Analytical elements of transient thermal impedance Z_{thJC} for DC

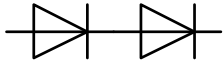
Pos. n	1	2	3	4	5	6	7
R_{thn} [K/W]	0,0426	0,0429	0,0257	0,0097	0,0031		
τ_n [s]	3,06	0,61	0,11	0,008	0,0009		

Analytische Funktion / Analytical function:
$$Z_{thJC} = \sum_{n=1}^{n_{max}} R_{thn} \left(1 - e^{-\frac{t}{\tau_n}} \right)$$



Transienter innerer Wärmewiderstand je Zweig / Transient thermal impedance per arm $Z_{thJC} = f(t)$

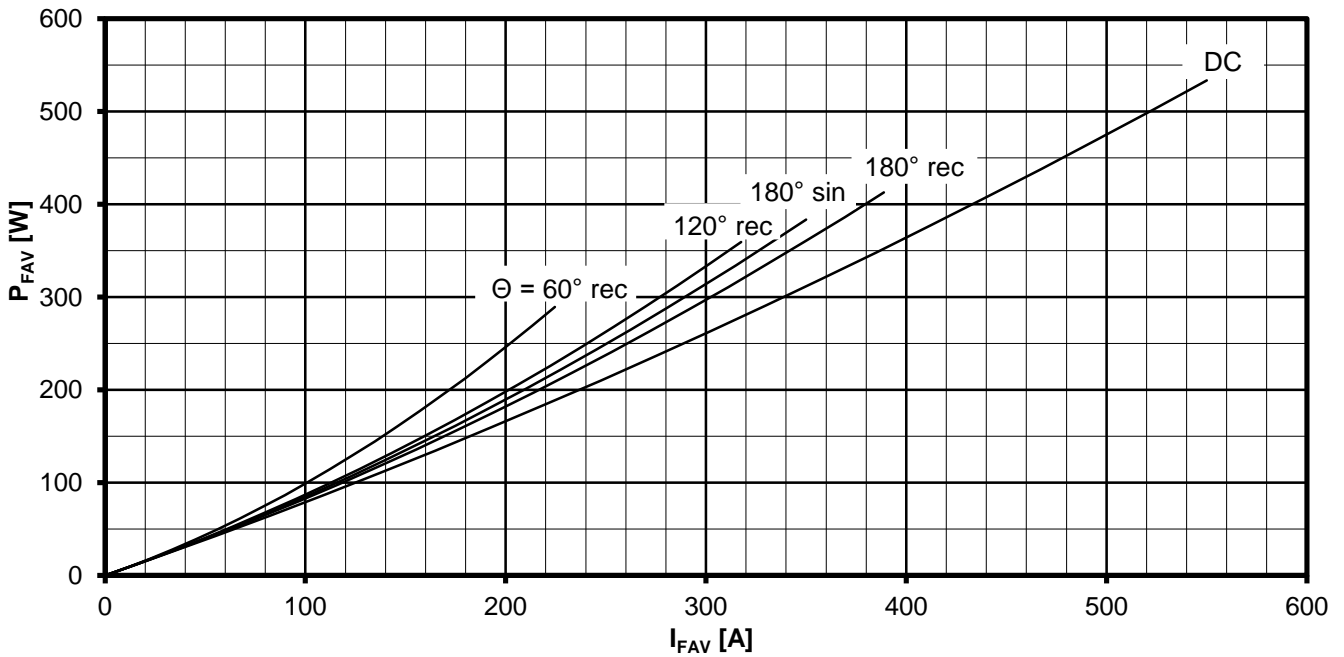
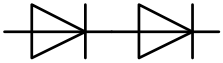
Parameter: Stromflußwinkel Θ / Current conduction angle Θ



Erhöhung des $Z_{th DC}$ bei Sinus und Rechteckströmen mit unterschiedlichen Stromflusswinkeln Θ
Rise of $Z_{th DC}$ for sinewave and rectangular current with different current conduction angles Θ
 $\Delta Z_{th \Theta rec} / \Delta Z_{th \Theta sin}$

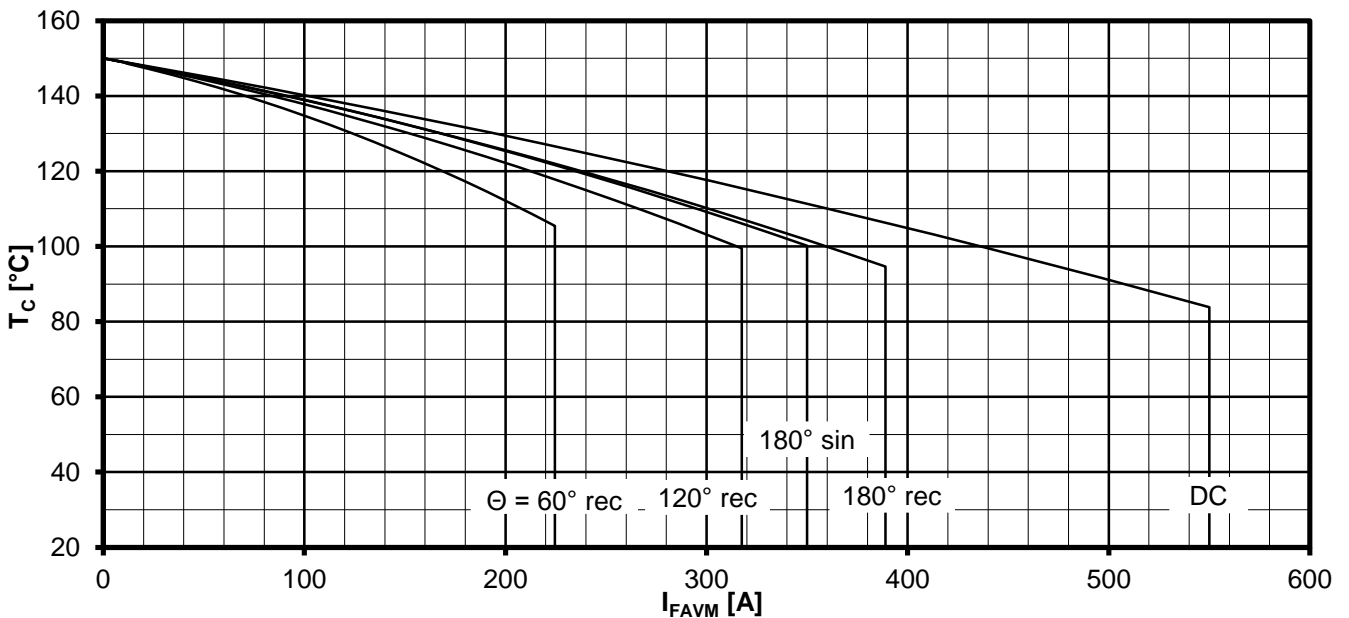
	$\Theta = 180^\circ$	$\Theta = 120^\circ$	$\Theta = 90^\circ$	$\Theta = 60^\circ$	$\Theta = 30^\circ$
$\Delta Z_{th \Theta rec}$ [K/W]	0,01007	0,01655	0,02161	0,02981	0,04541
$\Delta Z_{th \Theta sin}$ [K/W]	0,00600	0,01012	0,01749	0,02634	0,04321

$$Z_{th \Theta rec} = Z_{th DC} + \Delta Z_{th \Theta rec}$$
$$Z_{th \Theta sin} = Z_{th DC} + \Delta Z_{th \Theta sin}$$



Durchlassverlustleistung je Zweig / On-state power loss per arm $P_{FAV} = f(I_{FAV})$

Parameter: Stromflußwinkel / Current conduction angle Θ

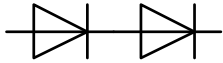


Höchstzulässige Gehäusetemperatur / Maximum allowable case temperature $T_c = f(I_{FAVM})$

Strombelastung je Zweig / Current load per arm

Berechnungsgrundlage P_{TAV}
Calculation base P_{TAV}

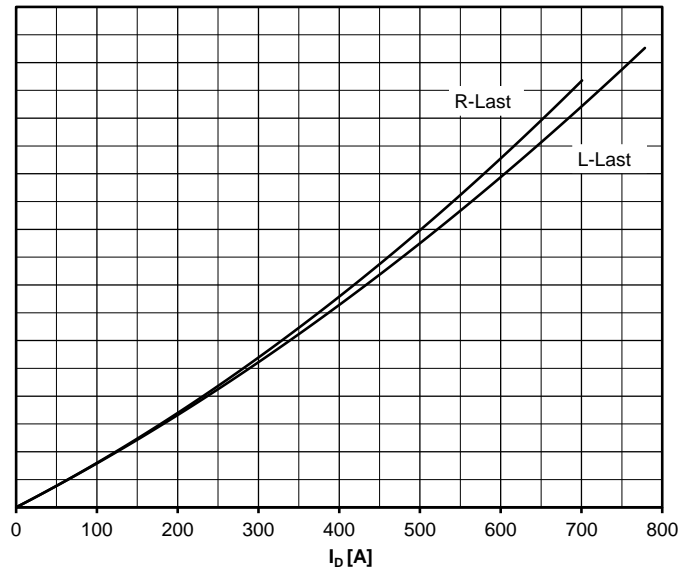
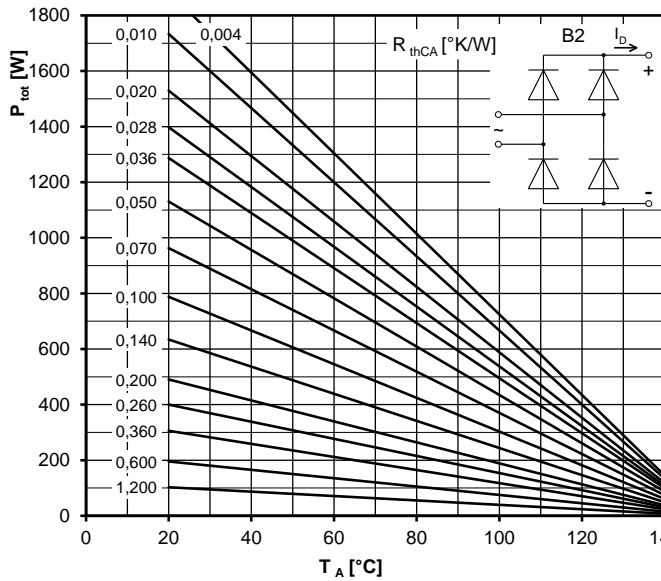
Parameter: Stromflußwinkel Θ / Current conduction angle Θ



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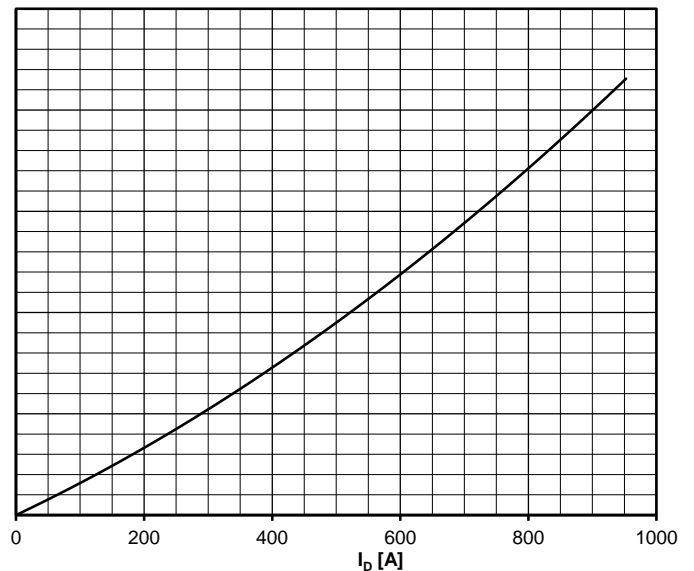
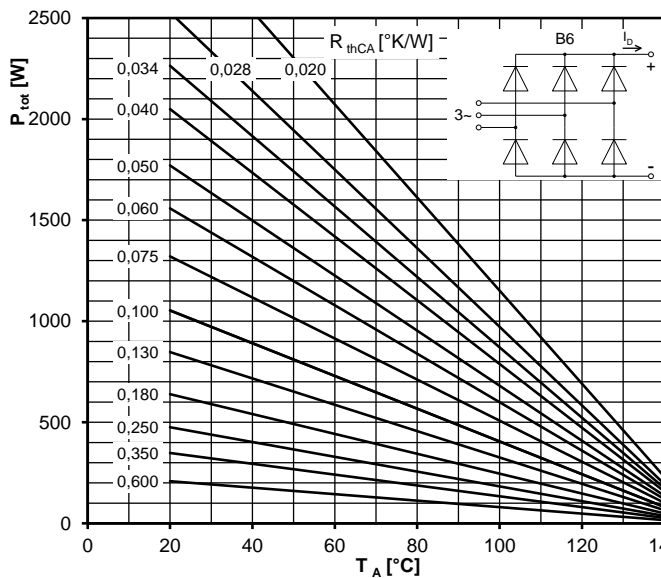
Höchstzulässiger Ausgangsstrom / Maximum rated output current I_b

B2- Zweipuls-Brückenschaltung / Two-pulse bridge circuit

Gesamtverlustleistung der Schaltung / Total power dissipation at circuit P_{tot}

Parameter:

Wärmewiderstand zwischen den Gehäusen und Umgebung / Thermal resistance cases to ambient R_{thCA}



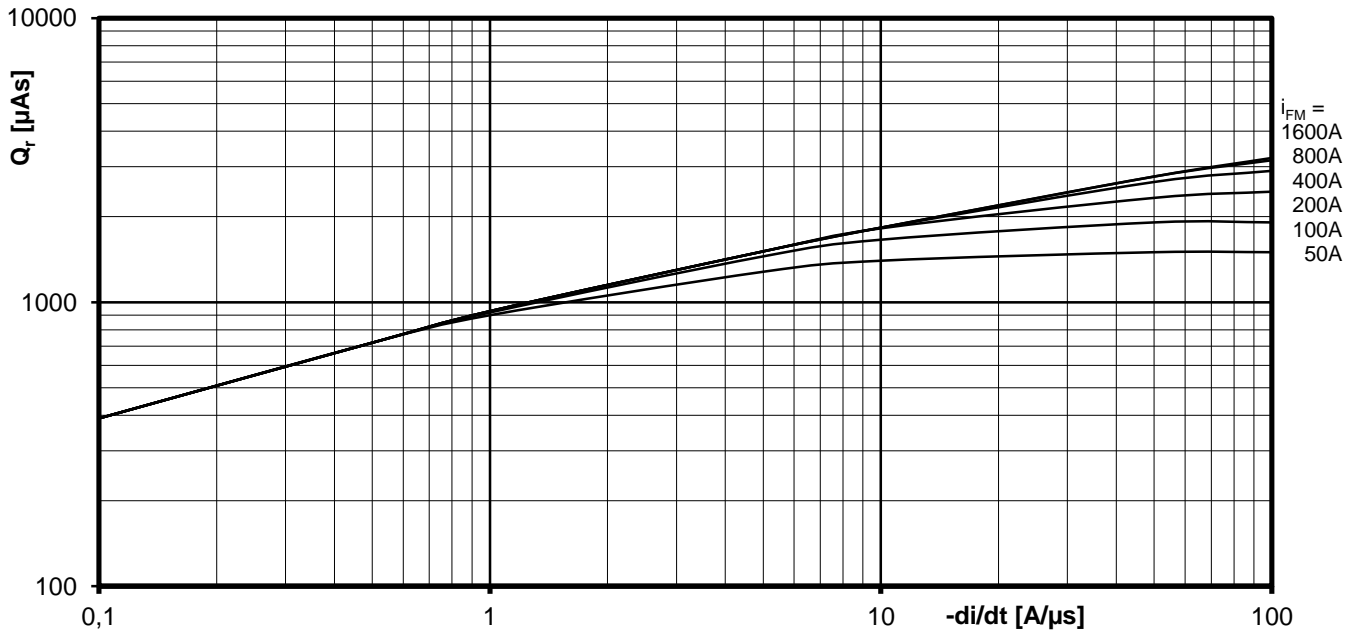
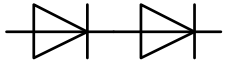
Höchstzulässiger Ausgangsstrom / Maximum rated output current I_b

B6- Sechspuls-Brückenschaltung / Six-pulse bridge circuit

Gesamtverlustleistung der Schaltung / Total power dissipation at circuit P_{tot}

Parameter:

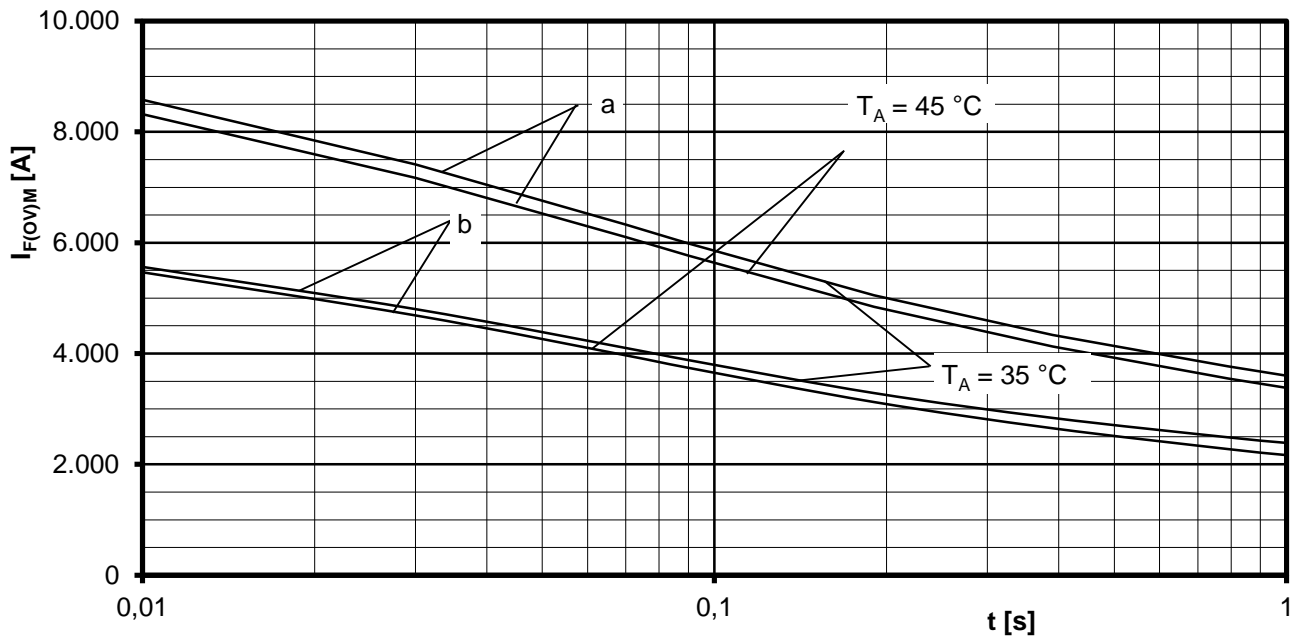
Wärmewiderstand zwischen den Gehäusen und Umgebung / Thermal resistance cases to ambient R_{thCA}



Sperrverzögerungsladung / Recovered charge $Q_r = f(-di/dt)$

$$T_{vj} = T_{vjmax}, V_R \leq 0,5 V_{RRM}, V_{RM} = 0,8 V_{RRM}$$

Parameter: Durchlaßstrom / On-state current i_{FM}



Grenzstrom je Zweig / Maximum overload on-state current per arm $I_{F(OV)M} = f(t), V_{RM} = 0,8 V_{RRM}$

a: Leerlauf / No-load conditions

b: Vorlaststrom je Zweig / Pre-load current per arm $I_{FAV(vor)} = I_{FAVM}$

$T_a = 35^\circ\text{C}$, verstärkte Luftkühlung / Forced air cooling Kühlkörper / Heatsink type: KM17 (Papst 4650)

$T_a = 45^\circ\text{C}$, natürliche Luftkühlung / Natural air cooling Kühlkörper / Heatsink type: KM17 (60W)